## EB13C3K1H-18.750M



Series -RoHS Compliant (Pb-free) Low Current 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability ±20ppm over -40°C to +85°C

### Logic Control / Additional Output Tri-State (High Impedance)

Nominal Frequency 18.750MHz

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Duty Cycle -50 ±10(%)

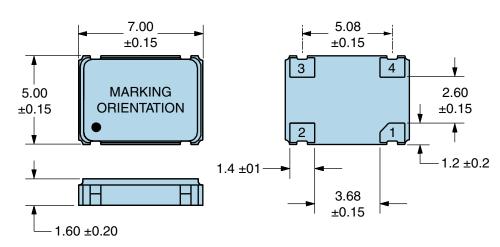
| Nominal Frequency                     | 18.750MHz   |
|---------------------------------------|---|
| Frequency Tolerance/Stability         | ±20ppm over -40°C to +85°C (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration) |
| Supply Voltage                        | 3.3Vdc ±10%   |
| Input Current                         | 3mA Maximum   |
| Output Voltage Logic High (Voh)       | 90% of Vdd Minimum  |
| Input Current Logic High (Ioh)        | -1.6mA  |
| Output Voltage Logic Low (Vol)        | 10% of Vdd Maximum  |
| Input Current Logic Low (IoI)         | +1.6mA  |
| Rise/Fall Time                        | 6nSec Maximum (Measured at 20% to 80% of waveform)  |
| Duty Cycle                            | 50 ±10(%) (Measured at 50% of waveform)   |
| Load Drive Capability                 | 15pF Maximum  |
| Output Logic Type                     | CMOS  |
| Logic Control / Additional Output     | Tri-State (High Impedance)  |
| Tri-State Input Voltage (Vih and Vil) | 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)  |
| Standby Current                       | 10µA Maximum (Disabled Output: High Impedance)  |
| One Sigma Clock Period Jitter         | 25pSec Maximum  |
| Start Up Time                         | 10mSec Maximum  |
| Storage Temperature Range             | -55°C to +125°C   |

| LINIKONMENTAL & MECHANICAL SPECIFICATIONS |                                       |  |
|---|---------------------------------------|--|
| Fine Leak Test                            | MIL-STD-883, Method 1014, Condition A |  |
| Gross Leak Test                           | MIL-STD-883, Method 1014, Condition C |  |
| Mechanical Shock                          | MIL-STD-202, Method 213, Condition C  |  |
| Resistance to Soldering Heat              | MIL-STD-202, Method 210               |  |
| Resistance to Solvents                    | MIL-STD-202, Method 215               |  |
| Solderability                             | MIL-STD-883, Method 2003              |  |
| Temperature Cycling                       | MIL-STD-883, Method 1010              |  |
| Vibration                                 | MIL-STD-883, Method 2007, Condition A |  |

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### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**

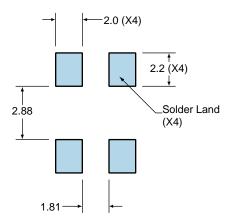


| PIN          | CONNECTION     |  |
|--------------|----------------|--|
| 1            | Tri-State      |  |
| 2            | Ground         |  |
| 3            | Output         |  |
| 4            | Supply Voltage |  |
| LINE MARKING |                |  |
| 1            | ECLIPTEK       |  |
|              |                |  |
| 2<br>3       | 18.750M        |  |

ZZ=Week of the Year

### Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1

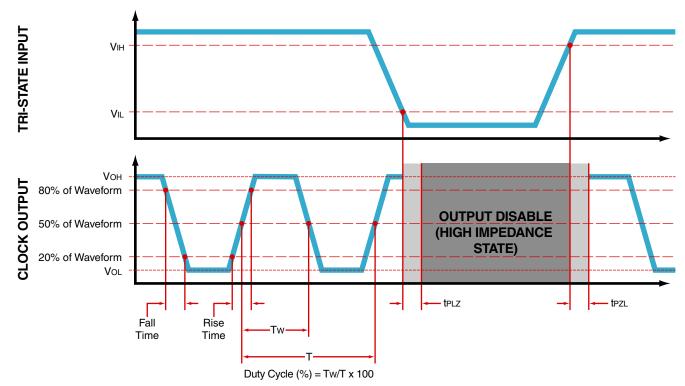


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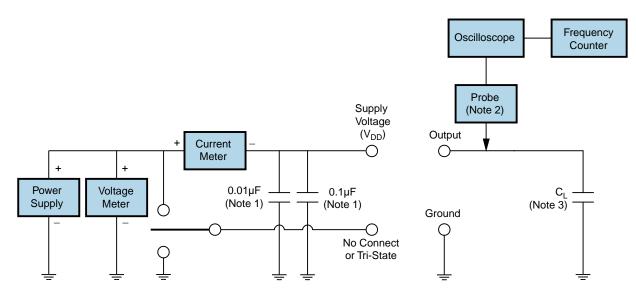
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#### **OUTPUT WAVEFORM & TIMING DIAGRAM**



**Test Circuit for CMOS Output** 



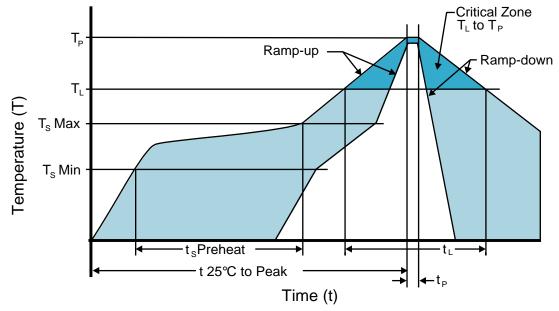
Note 1: An external  $0.1\mu$ F low frequency tantalum bypass capacitor in parallel with a  $0.01\mu$ F high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**



### **High Temperature Infrared/Convection**

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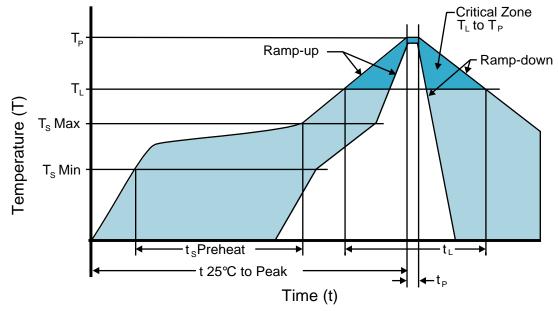
| <u> </u>  |   |
|---|---|
| T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)         | 3°C/second Maximum                                |
| Preheat   |   |
| - Temperature Minimum (T <sub>s</sub> MIN)                  | 150°C   |
| - Temperature Typical (T <sub>s</sub> TYP)                  | 175°C   |
| <ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul> | 200°C   |
| - Time (t <sub>s</sub> MIN)                                 | 60 - 180 Seconds                                  |
| Ramp-up Rate (T⊾ to T <sub>P</sub> )                        | 3°C/second Maximum                                |
| Time Maintained Above:                                      |   |
| - Temperature (T∟)  | 217°C   |
| - Time (t∟)   | 60 - 150 Seconds                                  |
| Peak Temperature (T <sub>P</sub> )                          | 260°C Maximum for 10 Seconds Maximum              |
| Target Peak Temperature (T <sub>P</sub> Target)             | 250°C +0/-5°C                                     |
| Time within 5°C of actual peak (t <sub>p</sub> )            | 20 - 40 seconds                                   |
| Ramp-down Rate  | 6°C/second Maximum                                |
| Time 25°C to Peak Temperature (t)                           | 8 minutes Maximum                                 |
| Moisture Sensitivity Level                                  | Level 1   |
| Additional Notes  | Temperatures shown are applied to body of device. |
|   |   |

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### **Recommended Solder Reflow Methods**

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### Low Temperature Infrared/Convection 240°C

| $T_s$ MAX to $T_L$ (Ramp-up Rate)                | 5°C/second Maximum                                     |
|--|--|
| Preheat  |  |
| - Temperature Minimum (T <sub>s</sub> MIN)       | N/A  |
| - Temperature Typical (T <sub>s</sub> TYP)       | 150°C  |
| - Temperature Maximum (T <sub>s</sub> MAX)       | N/A  |
| - Time (t <sub>s</sub> MIN)                      | 60 - 120 Seconds                                       |
| Ramp-up Rate (T⊾ to T <sub>P</sub> )             | 5°C/second Maximum                                     |
| Time Maintained Above:                           |  |
| - Temperature (T∟)                               | 150°C  |
| - Time (t∟)                                      | 200 Seconds Maximum                                    |
| Peak Temperature (T <sub>P</sub> )               | 240°C Maximum  |
| Target Peak Temperature (T <sub>P</sub> Target)  | 240°C Maximum 1 Time / 230°C Maximum 2 Times           |
| Time within 5°C of actual peak (t <sub>p</sub> ) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate                                   | 5°C/second Maximum                                     |
| Time 25°C to Peak Temperature (t)                | N/A  |
| Moisture Sensitivity Level                       | Level 1  |
| Additional Notes                                 | Temperatures shown are applied to body of device.      |

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)